Low-power configurable gate with voltage-level translatorRev. 4 — 15 august 2012Product data sheet

### 1. General description

The 74AUP1T98 provides low-power, low-voltage configurable logic gate functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to  $V_{CC}$  or GND.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 2.3 V to 3.6 V.

The 74AUP1T98 is designed for logic-level translation applications with input switching levels that accept 1.8 V low-voltage CMOS signals, while operating from either a single 2.5 V or 3.3 V supply voltage.

The wide supply voltage range ensures normal operation as battery voltage drops from 3.6 V to 2.3 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger inputs make the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range.

### 2. Features and benefits

- Wide supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I<sub>CC</sub> = 1.5 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power configurable gate with voltage-level translator

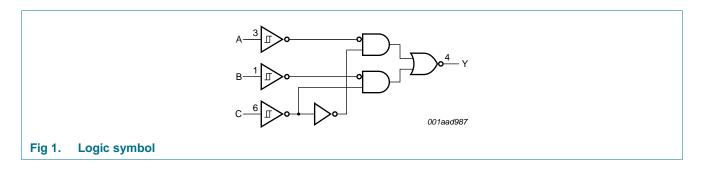
## 3. Ordering information

Table 1. Ordering information								
Type number	Package							
	Temperature range	Name	Description	Version				
74AUP1T98GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74AUP1T98GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886				
74AUP1T98GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891				
74AUP1T98GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AUP1T98GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				

### 4. Marking

Table 2. Marking	
Type number	Marking code
74AUP1T98GW	aR
74AUP1T98GM	aR
74AUP1T98GF	aR
74AUP1T98GN	aR
74AUP1T98GS	aR

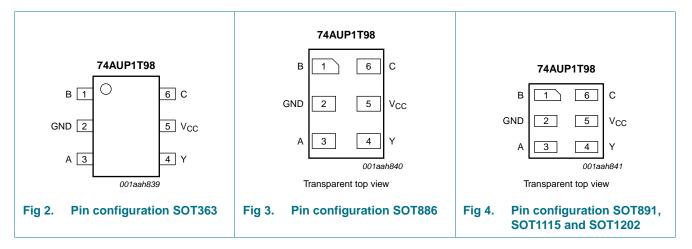
### 5. Functional diagram



Low-power configurable gate with voltage-level translator

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Symbol	Pin	Description
		- company
В	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V <sub>CC</sub>	5	supply voltage
С	6	data input

### 7. Functional description

Table 4.	Function table <sup>[1]</sup>		
Input			Output
С	В	Α	Y
L	L	L	Н
L	L	Н	Н
L	н	L	L
L	н	Н	L
Н	L	L	Н
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

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# 74AUP1T98

Low-power configurable gate with voltage-level translator

### 7.1 Logic configurations

### Table 5.Function selection table

Logic function	Figure
2-input MUX (inverting)	see <u>Figure 5</u>
2-input NAND	see <u>Figure 6</u>
2-input NOR with one input inverted	see Figure 7
2-input AND with one input inverted	see Figure 7
2-input NAND with one input inverted	see Figure 8
2-input OR with one input inverted	see Figure 8
2-input NOR	see Figure 9
Buffer	see Figure 10
Inverter	see Figure 11

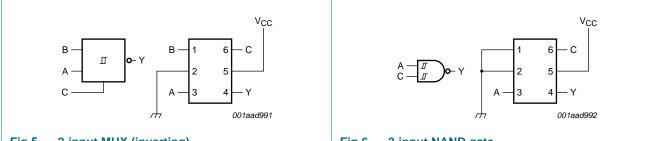


Fig 5. 2-input MUX (inverting)

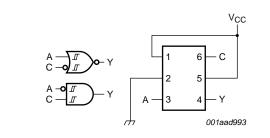


Fig 7. 2-input AND gate with input A inverted or 2-input NOR gate with input C inverted



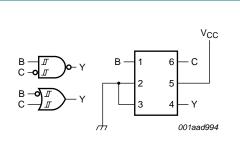
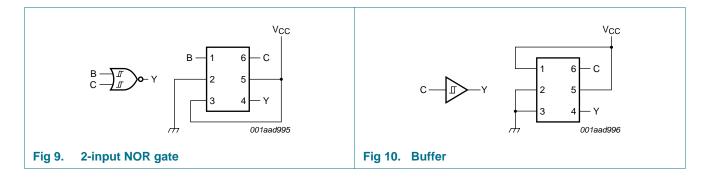
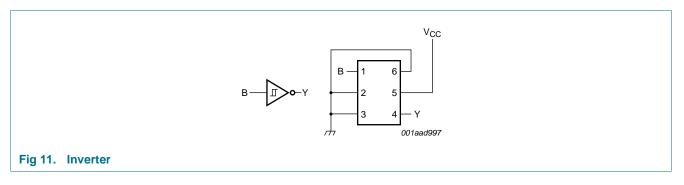


Fig 8. 2-input OR gate with input B inverted or 2-input NAND gate with input C inverted



Low-power configurable gate with voltage-level translator



#### **Limiting values** 8.

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	$V_{l} < 0 V$	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι <sub>ΟΚ</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 package: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

#### 9. **Recommended operating conditions**

#### Table 7. **Recommended operating conditions** Conditions Symbol Parameter Min Max supply voltage 2.3 3.6 Vcc input voltage 0 3.6 VI Vo output voltage Active mode 0 V<sub>CC</sub> Power-down mode; $V_{CC} = 0 V$ 0 3.6 -40 Tamb ambient temperature +125

Unit

V

V

V

V

°C

#### Low-power configurable gate with voltage-level translator

## **10. Static characteristics**

### Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	S ℃					
V <sub>T+</sub>	positive-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.75	-	1.16	V
V <sub>T-</sub>	negative-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.35	-	0.60	V
	voltage	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_H=V_{T+}-V_{T-})$				
		$V_{CC}$ = 2.3 V to 2.7 V	0.23	-	0.60	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.25	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+} \text{ or } V_{T-}$				
		$I_{O}$ = –20 $\mu A;~V_{CC}$ = 2.3 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_0$ = 20 $\mu$ A; $V_{CC}$ = 2.3 V to 3.6 V	-	-	0.10	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I <sub>I</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.1	μA
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$V_{I} = \text{GND or } V_{\text{CC}}; I_{\text{O}} = 0 \text{ A};$ $V_{\text{CC}} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	1.2	μA
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_I$ = GND or $V_{CC}$	-	0.8	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
V <sub>T+</sub>	positive-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.35	-	0.60	V
	voltage	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$				
		$V_{CC}$ = 2.3 V to 2.7 V	0.10	-	0.60	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.15			

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## 74AUP1T98

### Low-power configurable gate with voltage-level translator

#### Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>он</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = –20 $\mu A;  V_{CC}$ = 2.3 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.97	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu A;$ $V_{CC}$ = 2.3 V to 3.6 V	-	-	0.1	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		$I_{O}$ = 3.1 mA; $V_{CC}$ = 2.3 V	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.45	V
I <sub>I</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.5	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	1.5	μΑ
Δl <sub>CC</sub>	additional supply current	$V_{CC}$ = 2.3 V to 2.7 V; $I_{O}$ = 0 A	<u>[1]</u> -	-	4	μΑ
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}; I_{O} = 0 \text{ A}$	[2] _	-	12	μA
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>T+</sub>	positive-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold	$V_{CC}$ = 2.3 V to 2.7 V	0.33	-	0.64	V
	voltage	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.46	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$				
		$V_{CC}$ = 2.3 V to 2.7 V	0.10	-	0.60	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	0.15	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = –20 $\mu\text{A};V_{CC}$ = 2.3 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu A; V_{CC}$ = 2.3 V to 3.6 V	-	-	0.11	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.36	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
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At recom	mended operating conditions	s; voltages are referenced to GND (grou	und = 0 V).			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>OFF</sub>	power-off leakage current	$V_{I} \text{ or } V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μA
$\Delta I_{OFF}$	additional power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	3.5	μA
$\Delta I_{CC}$	additional supply current	$V_{CC}$ = 2.3 V to 2.7 V; $I_O$ = 0 A	<u>[1]</u> -	-	7	μA
		$V_{CC} = 3.0 \text{ V}$ to 3.6 V; $I_{O} = 0 \text{ A}$	[2] _	-	22	μA

#### Table 8. Static characteristics ... continued

[1] One input at 0.3 V or 1.1 V, other input at  $V_{CC} \mbox{ or GND}.$ 

[2] One input at 0.45 V or 1.2 V, other input at V<sub>CC</sub> or GND.

### **11. Dynamic characteristics**

#### Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

o 2.7 V; V <sub>I</sub> = 2.3	A, B, C to Y; see Figure 12 $C_L = 5 \text{ pF}$ $C_L = 10 \text{ pF}$ $C_L = 15 \text{ pF}$ $C_L = 30 \text{ pF}$	[2]	Min 2.0 2.5 2.9 3.9 1.7 2.1 2.5	<b>Typ</b> <sup>[1]</sup> 3.6 4.2 4.6 5.8 3.4 4.0	Max 5.7 6.3 6.9 8.3 5.6 6.3	Min 0.5 1.0 1.5 0.5 1.0	Max (85 °C) 6.8 7.9 8.7 10.8 6.0	Max (125 °C) 7.5 8.7 9.6 11.9 6.6	ns ns ns ns ns
pagation delay to 2.7 V; V <sub>I</sub> = 2.3	$ \begin{array}{c} \text{A, B, C to Y; see Figure 12} \\ \hline C_L = 5 \text{ pF} \\ \hline C_L = 10 \text{ pF} \\ \hline C_L = 15 \text{ pF} \\ \hline C_L = 30 \text{ pF} \\ \hline \end{array} \\ \hline \begin{array}{c} \text{SV to 2.7 V} \\ \text{A, B, C to Y; see Figure 12} \\ \hline \end{array} \\ \hline \\ \hline \\ C_L = 5 \text{ pF} \\ \hline \end{array} \\ \hline \\ \hline \\ C_L = 10 \text{ pF} \\ \hline \end{array} \\ \hline \\ \hline \\ \hline \\ C_L = 15 \text{ pF} \\ \hline \end{array} $		2.5 2.9 3.9 1.7 2.1	4.2 4.6 5.8 3.4	6.3 6.9 8.3 5.6	1.0 1.0 1.5 0.5	7.9 8.7 10.8 6.0	8.7 9.6 11.9	ns ns ns
o 2.7 V; V <sub>I</sub> = 2.3	$C_{L} = 5 \text{ pF}$ $C_{L} = 10 \text{ pF}$ $C_{L} = 15 \text{ pF}$ $C_{L} = 30 \text{ pF}$ <b>3 V to 2.7 V</b> $A, B, C \text{ to Y; see Figure 12}$ $C_{L} = 5 \text{ pF}$ $C_{L} = 10 \text{ pF}$ $C_{L} = 15 \text{ pF}$		2.5 2.9 3.9 1.7 2.1	4.2 4.6 5.8 3.4	6.3 6.9 8.3 5.6	1.0 1.0 1.5 0.5	7.9 8.7 10.8 6.0	8.7 9.6 11.9	ns ns ns
-	$C_{L} = 10 \text{ pF}$ $C_{L} = 15 \text{ pF}$ $C_{L} = 30 \text{ pF}$ <b>3 V to 2.7 V</b> A, B, C to Y; see Figure 12 $C_{L} = 5 \text{ pF}$ $C_{L} = 10 \text{ pF}$ $C_{L} = 15 \text{ pF}$	[2]	2.5 2.9 3.9 1.7 2.1	4.2 4.6 5.8 3.4	6.3 6.9 8.3 5.6	1.0 1.0 1.5 0.5	7.9 8.7 10.8 6.0	8.7 9.6 11.9	ns ns ns
-	$C_{L} = 15 \text{ pF}$ $C_{L} = 30 \text{ pF}$ <b>3 V to 2.7 V</b> A, B, C to Y; see Figure 12 $C_{L} = 5 \text{ pF}$ $C_{L} = 10 \text{ pF}$ $C_{L} = 15 \text{ pF}$	[2]	2.9 3.9 1.7 2.1	4.6 5.8 3.4	6.9 8.3 5.6	1.0 1.5 0.5	8.7 10.8 6.0	9.6 11.9	ns ns
-	$C_{L} = 30 \text{ pF}$ <b>3 V to 2.7 V</b> A, B, C to Y; see Figure 12 C_{L} = 5 \text{ pF} C_{L} = 10 \text{ pF} C_{L} = 15 \text{ pF}	[2]	3.9 1.7 2.1	5.8	8.3 5.6	1.5 0.5	10.8 6.0	11.9	ns
-		[2]	1.7 2.1	3.4	5.6	0.5	6.0		
-	A, B, C to Y; see Figure 12 $C_L = 5 \text{ pF}$ $C_L = 10 \text{ pF}$ $C_L = 15 \text{ pF}$	[2]	2.1					6.6	ns
pagation delay	$C_L = 5 \text{ pF}$ $C_L = 10 \text{ pF}$ $C_L = 15 \text{ pF}$	[2]	2.1					6.6	ns
	$C_L = 10 \text{ pF}$ $C_L = 15 \text{ pF}$		2.1					6.6	ns
	C <sub>L</sub> = 15 pF			4.0	6.3	10	74		
			25			1.0	7.1	7.9	ns
	C = 20  pE		2.5	4.5	6.9	1.0	7.9	8.7	ns
	$C_L = 30  \text{pr}$		3.4	5.6	8.4	1.5	10.0	11.0	ns
o 2.7 V; V <sub>I</sub> = 3.0	) V to 3.6 V								
propagation delay	A, B, C to Y; see Figure 12	[2]							
	C <sub>L</sub> = 5 pF		1.3	3.2	5.2	0.5	5.5	6.1	ns
	C <sub>L</sub> = 10 pF		1.8	3.7	5.9	1.0	6.5	7.2	ns
	C <sub>L</sub> = 15 pF		2.2	4.2	6.5	1.0	7.4	8.2	ns
	C <sub>L</sub> = 30 pF		3.1	5.4	7.9	1.5	9.5	10.5	ns
:o 3.6 V; V <sub>I</sub> = 1.6	65 V to 1.95 V								
pagation delay	A, B, C to Y; see Figure 12	[2]							
	C <sub>L</sub> = 5 pF		2.0	2.9	4.1	0.5	8.0	8.8	ns
	C <sub>L</sub> = 10 pF		2.4	3.5	4.8	1.0	8.5	9.4	ns
	C <sub>L</sub> = 15 pF		2.8	3.9	5.4	1.0	9.1	10.1	ns
	C <sub>L</sub> = 30 pF		3.6	5.1	6.9	1.5	9.8	10.8	ns
		$C_{L} = 30 \text{ pF}$ $c_{L} = 5 \text{ pF}$ $c_{L} = 10 \text{ pF}$ $c_{L} = 15 \text{ pF}$	$C_{L} = 30 \text{ pF}$ $c_{L} = 5 \text{ pF}$ $c_{L} = 10 \text{ pF}$ $c_{L} = 15 \text{ pF}$	$C_{L} = 30 \text{ pF} \qquad 3.1$ $c_{L} = 30 \text{ pF} \qquad 3.1$ $c_{L} = 30 \text{ pF} \qquad 3.1$ $c_{L} = 30 \text{ pF} \qquad 2.0$ $C_{L} = 5 \text{ pF} \qquad 2.0$ $C_{L} = 10 \text{ pF} \qquad 2.4$ $C_{L} = 15 \text{ pF} \qquad 2.8$	$C_{L} = 30 \text{ pF} \qquad 3.1 \qquad 5.4$ $D 3.6 \text{ V; } \text{V}_{I} = 1.65 \text{ V to } 1.95 \text{ V}$ $D agation delay \qquad A, B, C \text{ to } \text{ Y; see Figure } 12 \qquad [2] \qquad C_{L} = 5 \text{ pF} \qquad 2.0 \qquad 2.9 \qquad C_{L} = 10 \text{ pF} \qquad 2.4 \qquad 3.5 \qquad C_{L} = 15 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 15 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad (C_{L} = 10 \text{ pF} \qquad C_{L} = 10 $	$C_{L} = 30 \text{ pF} \qquad 3.1 \qquad 5.4 \qquad 7.9$ $D 3.6 \text{ V; V}_{I} = 1.65 \text{ V to } 1.95 \text{ V}$ $C_{L} = 5 \text{ pF} \qquad 2.0 \qquad 2.9 \qquad 4.1$ $C_{L} = 10 \text{ pF} \qquad 2.4 \qquad 3.5 \qquad 4.8$ $C_{L} = 15 \text{ pF} \qquad 2.8 \qquad 3.9 \qquad 5.4$	$C_{L} = 30 \text{ pF} \qquad 3.1 \qquad 5.4 \qquad 7.9 \qquad 1.5$ $D 3.6 \text{ V; V}_{I} = 1.65 \text{ V to } 1.95 \text{ V}$ $D agation delay \qquad A, B, C \text{ to } Y; \text{ see Figure } 12 \qquad [2] \qquad \qquad$	$C_L = 30 \text{ pF}$ 3.1       5.4       7.9       1.5       9.5 <b>o 3.6 V; V_I = 1.65 V to 1.95 V</b> pagation delay       A, B, C to Y; see Figure 12       [2] $C_L = 5 \text{ pF}$ 2.0       2.9       4.1       0.5       8.0 $C_L = 10 \text{ pF}$ 2.4       3.5       4.8       1.0       8.5 $C_L = 15 \text{ pF}$ 2.8       3.9       5.4       1.0       9.1	$C_{L} = 30 \text{ pF} \qquad 3.1 \qquad 5.4 \qquad 7.9 \qquad 1.5 \qquad 9.5 \qquad 10.5$ $pagation delay \qquad A, B, C to Y; see Figure 12 \qquad [2] \qquad \qquad$

74AUP1T98 Product data sheet

#### Low-power configurable gate with voltage-level translator

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
V <sub>CC</sub> = 3.	0 V to 3.6 V; V <sub>I</sub> = 2.3	3 V to 2.7 V		1					
t <sub>pd</sub>	propagation delay	A, B, C to Y; see Figure 12	[2]						
		$C_L = 5 \text{ pF}$	1.5	2.8	4.4	0.5	5.3	5.9	ns
		C <sub>L</sub> = 10 pF	2.0	3.4	5.1	1.0	6.1	6.8	ns
		C <sub>L</sub> = 15 pF	2.4	3.9	5.7	1.0	6.8	7.5	ns
		C <sub>L</sub> = 30 pF	3.4	5.0	7.2	1.5	8.5	9.4	ns
$V_{\rm CC} = 3.$	0 V to 3.6 V; V <sub>I</sub> = 3.0	) V to 3.6 V							
t <sub>pd</sub>	propagation delay	A, B, C to Y; see Figure 12	[2]						
		C <sub>L</sub> = 5 pF	1.3	2.8	4.4	0.5	4.7	5.2	ns
		C <sub>L</sub> = 10 pF	1.7	3.3	5.2	1.0	5.7	6.3	ns
		C <sub>L</sub> = 15 pF	2.1	3.8	5.8	1.0	6.2	6.9	ns
		C <sub>L</sub> = 30 pF	3.1	5.0	7.2	1.5	7.8	8.6	ns
T <sub>amb</sub> = 2	25 °C								
C <sub>PD</sub>	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]						
	capacitance	$V_{CC}$ = 2.3 V to 2.7 V	-	3.6	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.3	-	-	-	-	pF

#### Table 9. Dynamic characteristics ...continued

[1] All typical values are measured at nominal  $V_{CC}$ .

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ 

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_o) \text{ where:}$ 

 $f_i = input frequency in MHz;$ 

 $f_o$  = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

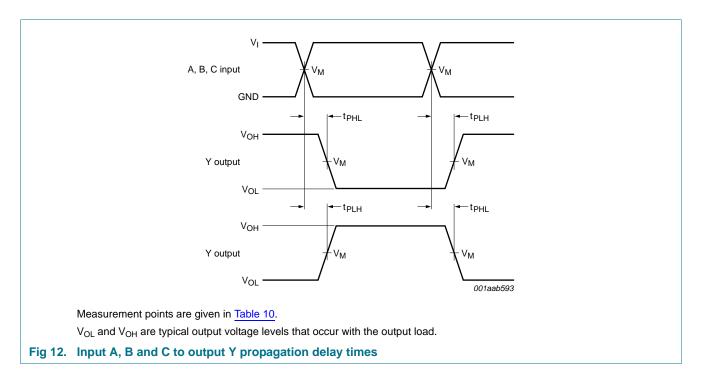
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

Low-power configurable gate with voltage-level translator

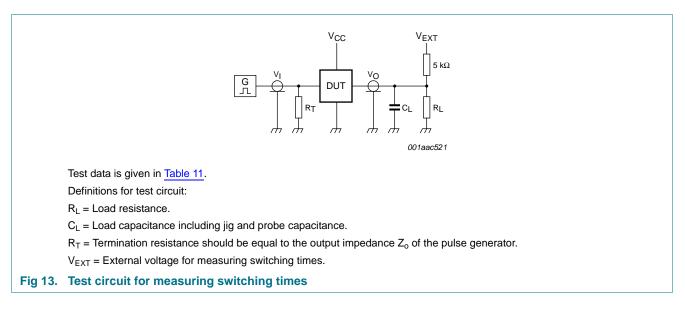
## 12. Waveforms



#### Table 10. Measurement points

Supply voltage	Output	Input					
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	t <sub>r</sub> = t <sub>f</sub>			
2.3 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_I$	1.65 V to 3.6 V	≤ 3.0 ns			

#### Low-power configurable gate with voltage-level translator



### Table 11. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
2.3 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 k\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 M\Omega$ .

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## 74AUP1T98

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### 13. Package outline

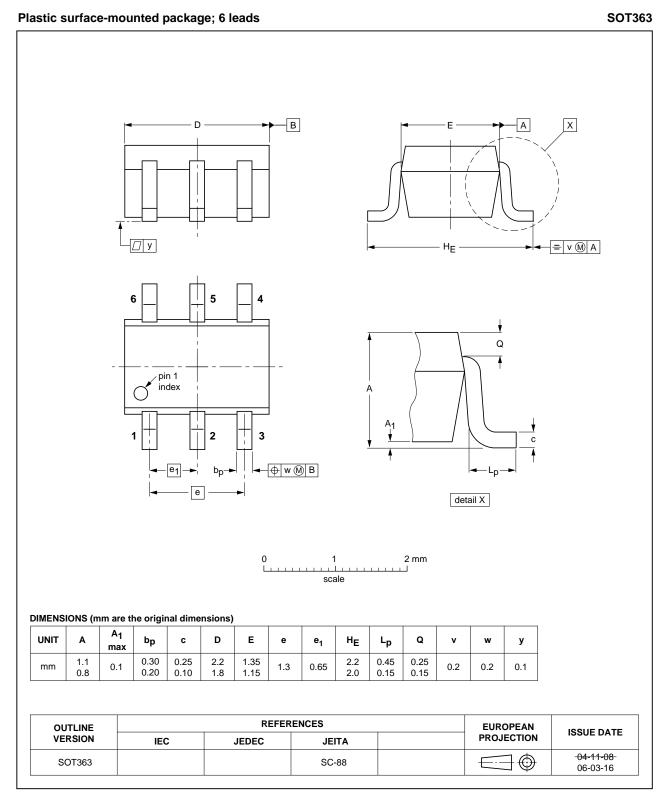
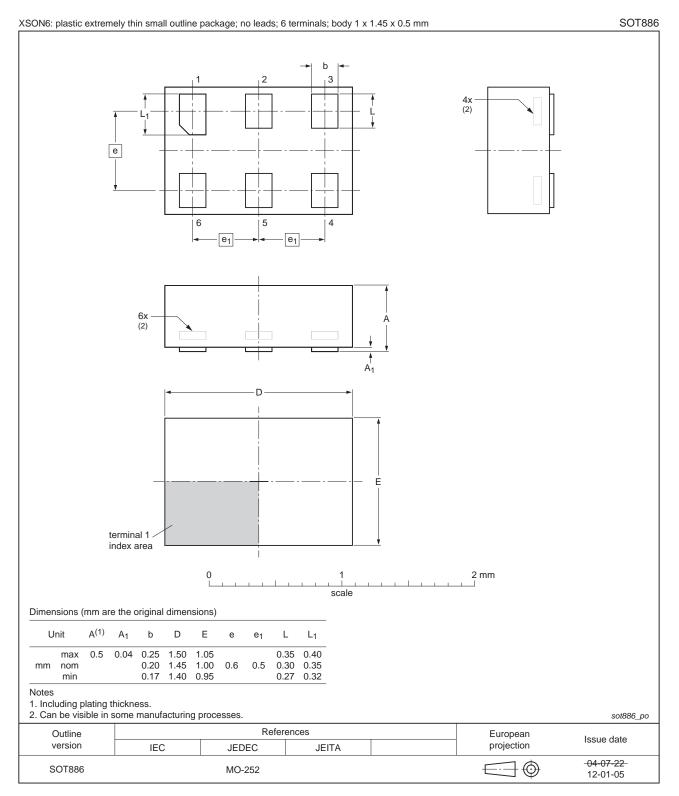


Fig 14. Package outline SOT363 (SC-88)

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74AUP1T98

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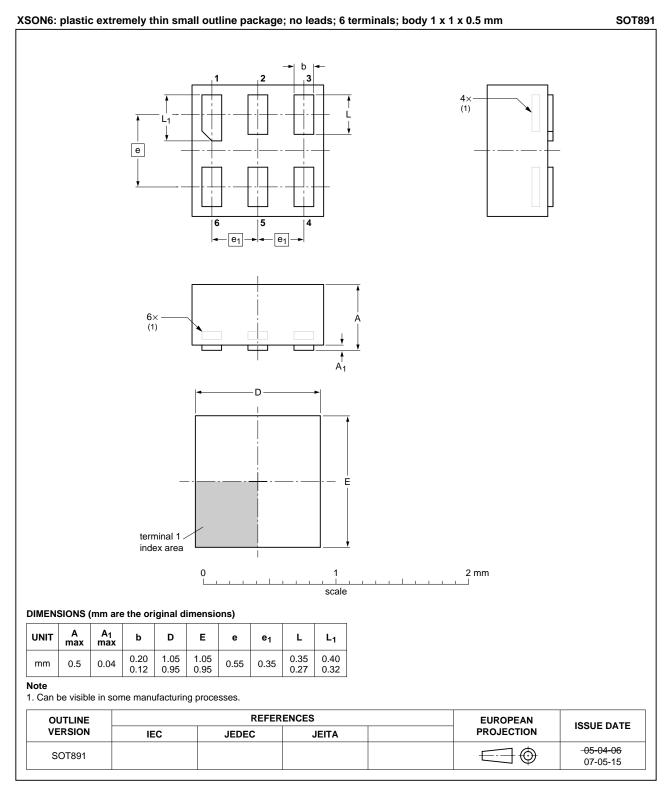


### Fig 15. Package outline SOT886 (XSON6)

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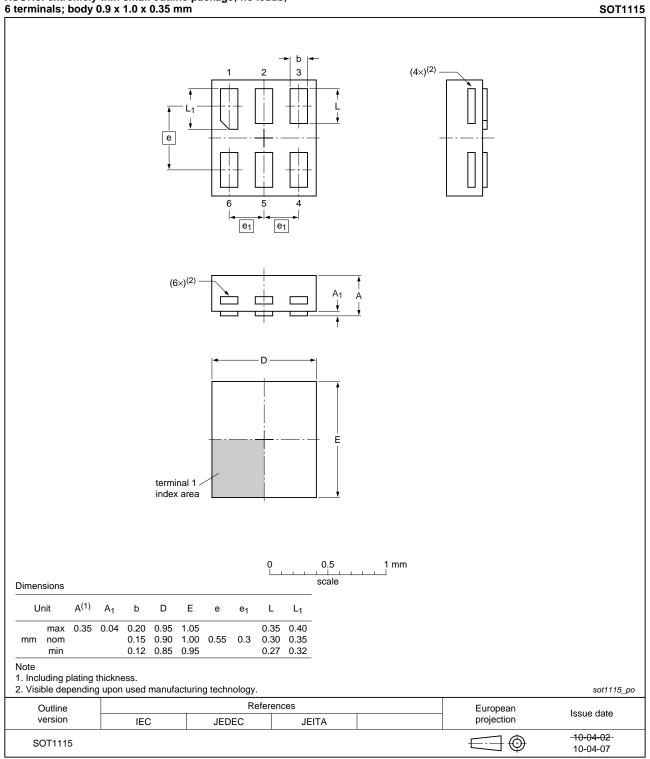
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#### Fig 16. Package outline SOT891 (XSON6)

74AUP1T98 Product data sheet

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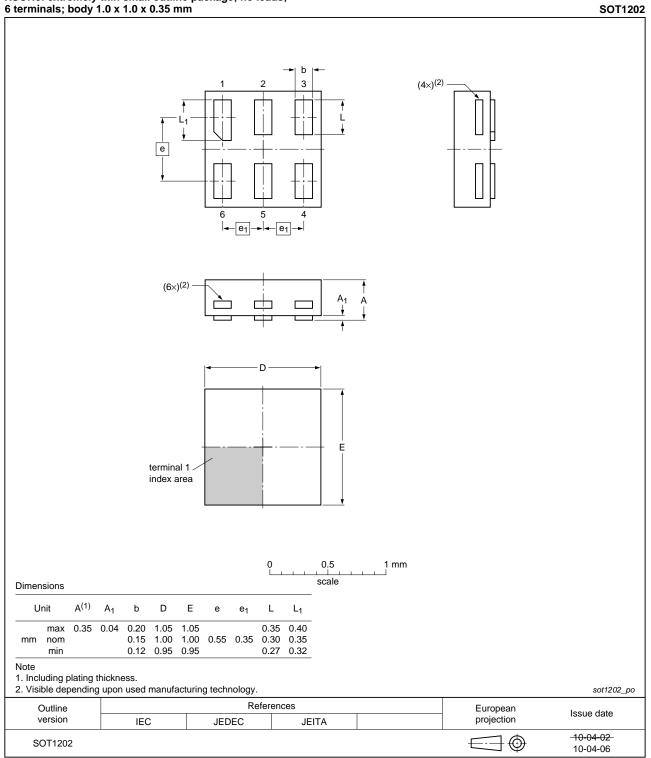
XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1115 (XSON6)

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74AUP1T98

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 18. Package outline SOT1202 (XSON6)

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## 14. Abbreviations

Table 12. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	

## 15. Revision history

Table 13. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T98 v.4	20120815	Product data sheet	-	74AUP1T98 v.3
Modifications:	<ul> <li>Package out</li> </ul>	line drawing of SOT886 (Figur	re 15) modified.	
74AUP1T98 v.3	20111130	Product data sheet	-	74AUP1T98 v.2
74AUP1T98 v.2	20101019	Product data sheet	-	74AUP1T98 v.1
74AUP1T98 v.1	20080306	Product data sheet	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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74AUP1T98

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### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning
6.2	Pin description 3
7	Functional description 3
7.1	Logic configurations 4
8	Limiting values 5
9	Recommended operating conditions 5
10	Static characteristics 6
11	Dynamic characteristics 8
12	Waveforms 10
13	Package outline 12
14	Abbreviations 17
15	Revision history 17
16	Legal information 18
16.1	Data sheet status 18
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks 19
17	Contact information 19
18	Contents

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